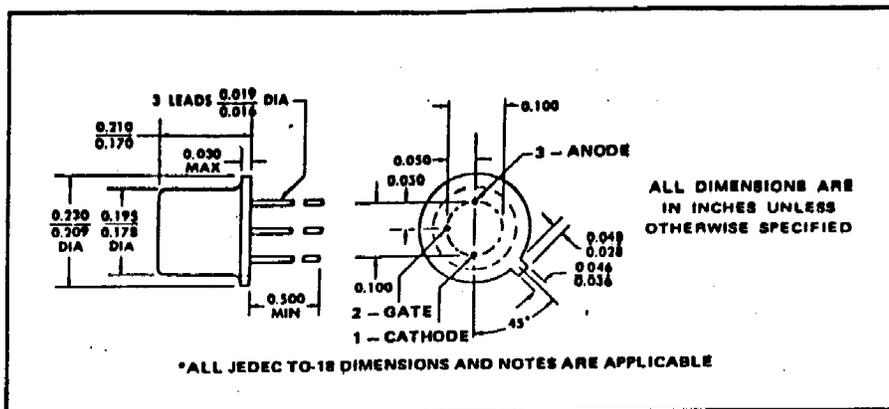


2N3008

SILICON REVERSE-BLOCKING TRIODE THYRISTOR



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

	2N3008	UNIT
*Static Off-State Voltage, V_D (See Note 1)	200	V
*Repetitive Peak Off-State Voltage, V_{DRM} (See Note 1)	200	V
*Static Reverse Voltage, V_R (See Note 2)	200	V
*Repetitive Peak Reverse Voltage, V_{RRM} (See Note 2)	200	V
*Continuous or RMS On-State Current at (or below) 55°C Free-Air Temperature ¹	350	mA
*Average On-State Current (180° Conduction Angle) at (or below) 55°C Free-Air Temperature ¹	250	mA
*Surge On-State Current (See Note 3)	6	A
Peak Negative Gate Voltage	8	V
*Peak Positive Gate Current (Pulse Width < 8 ms)	250	mA
*Average Gate Power Dissipation	100	mW
*Operating Free-Air Temperature Range	-65 to 200	°C
*Storage Temperature Range	-65 to 175	°C
*Lead Temperature 1/16 Inch from Case for 10 Seconds	300	°C

NOTES: 1. These values apply when the gate-cathode resistance $R_{GK} < 1 \text{ k}\Omega$.
 2. These values apply when the gate-cathode resistance $R_{GK} < \infty$.
 3. This value applies for one 60-Hz half sine wave when the device is operating at (or below) rated values of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
 *JEDEC registered data. This data sheet contains all applicable registered data in effect at the time of publication.

*electrical characteristics at 25°C free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_D Static Off-State Current	$V_D = \text{Rated } V_D, R_{GK} = 1 \text{ k}\Omega$			0.1	μA
	$V_D = \text{Rated } V_D, R_{GK} = 1 \text{ k}\Omega, T_A = 150^\circ\text{C}$			100	
I_G Gate Current ¹	$V_G = -5 \text{ V}, I_A = 0$			-5	μA
I_{GT} Gate Trigger Current	$V_{AA} = 5 \text{ V}, R_L = 12 \Omega, t_{p(g)} \geq 10 \mu\text{s}$			90	μA
	$V_{AA} = 5 \text{ V}, R_L = 12 \Omega, t_{p(g)} \geq 10 \mu\text{s}, T_A = -65^\circ\text{C}$			200	
V_{GT} Gate Trigger Voltage	$V_{AA} = 5 \text{ V}, R_L = 12 \Omega, t_{p(g)} \geq 10 \mu\text{s}, T_A = -65^\circ\text{C}$			0.9	V
	$V_{AA} = 5 \text{ V}, R_L = 12 \Omega, t_{p(g)} \geq 10 \mu\text{s}$			0.6	
	$V_{AA} = 5 \text{ V}, R_L = 12 \Omega, t_{p(g)} \geq 10 \mu\text{s}, T_A = 150^\circ\text{C}$	0.2		0.8	
I_H Holding Current	$R_{GK} = 1 \text{ k}\Omega, R_L = 2 \text{ k}\Omega$			1.8	mA
	$R_{GK} = 1 \text{ k}\Omega, R_L = 2 \text{ k}\Omega, T_A = -65^\circ\text{C}$			5	
V_T On-State Voltage	$I_T = 350 \text{ mA}, R_{GK} > 1 \text{ k}\Omega$, See Note 6			1.2	V

NJ Semi-Conductors reserves the right to change test conditions, parameters limits and package dimensions without notice information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

